



SANYO Semiconductors

DATA SHEET

P-Channel Silicon MOSFET

ECH8631 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 2.5V drive.
- Composite type, facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-40	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm²×0.8mm) 1unit	1.3	W
Total Power Dissipation	P _T	Mounted on a ceramic board (900mm²×0.8mm)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0	-12			V
Zero-Gate Voltage Drain Current	I _{DSS1}	V _{DS} =-4V, V _{GS} =0			-1	μA
	I _{DSS2}	V _{DS} =-12V, V _{GS} =0			-10	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-6V, I _D =-2.5A	5.5	9.3		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-2A, V _{GS} =-5V		24	30	mΩ
	R _{DS(on)2}	I _D =-1A, V _{GS} =-4.5V		26	34	mΩ
	R _{DS(on)3}	I _D =-0.5A, V _{GS} =-2.5V		42	56	mΩ
Input Capacitance	C _{iss}	V _{DS} =-6V, f=1MHz		1720		pF
Output Capacitance	C _{oss}	V _{DS} =-6V, f=1MHz		762		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-6V, f=1MHz		720		pF

Marking : FZ

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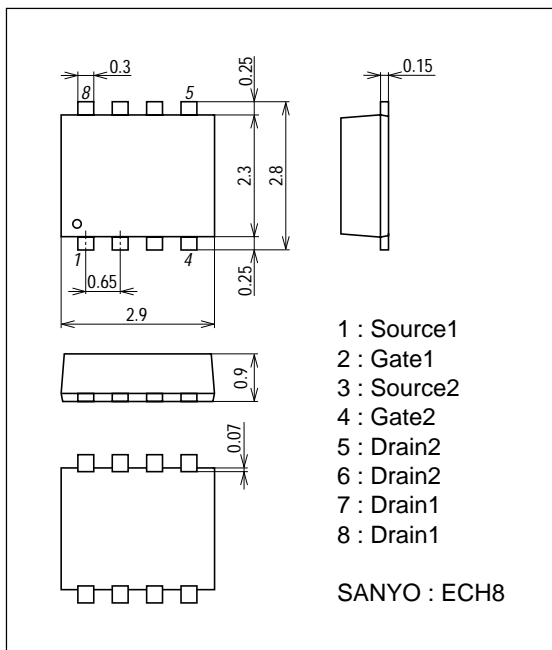
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		20		ns
Rise Time	t_r	See specified Test Circuit.		129		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		181		ns
Fall Time	t_f	See specified Test Circuit.		239		ns
Total Gate Charge	Q_g	$V_{DS}=-6V, V_{GS}=-5V, I_D=-5A$		19.6		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-6V, V_{GS}=-5V, I_D=-5A$		3.64		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-6V, V_{GS}=-5V, I_D=-5A$		5.82		nC
Diode Forward Voltage	V_{SD}	$I_S=-5A, V_{GS}=0$		-0.83	-1.5	V

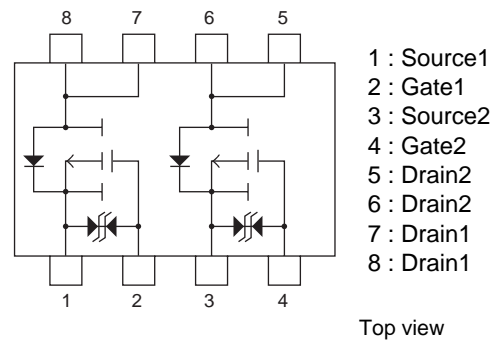
Package Dimensions

unit : mm

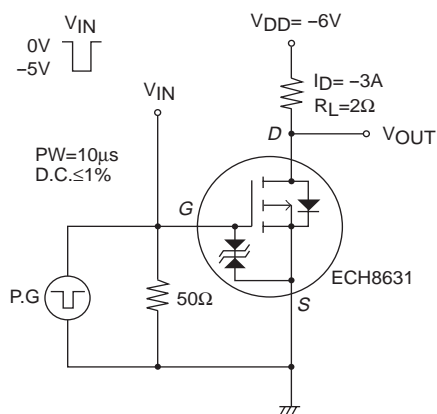
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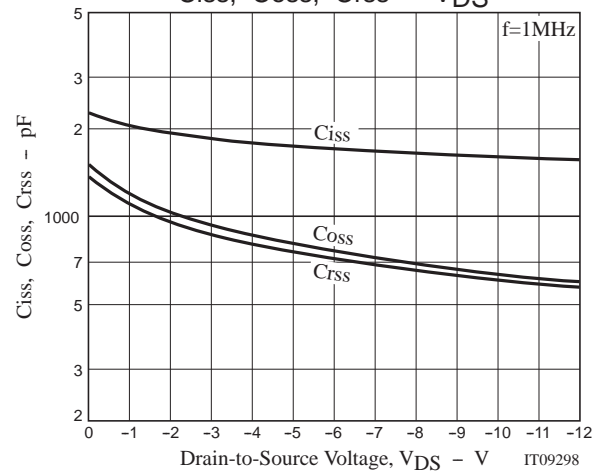
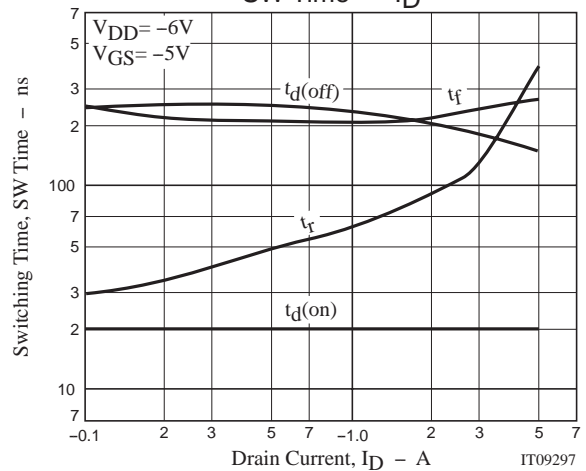
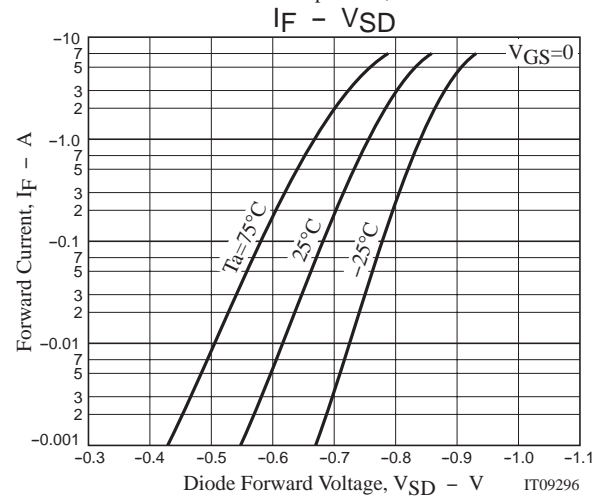
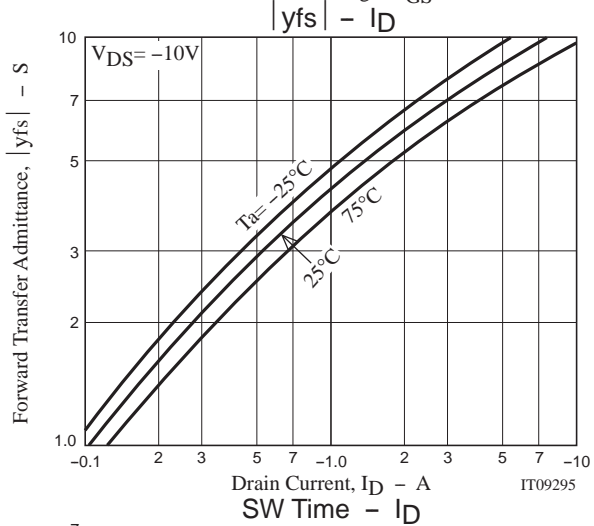
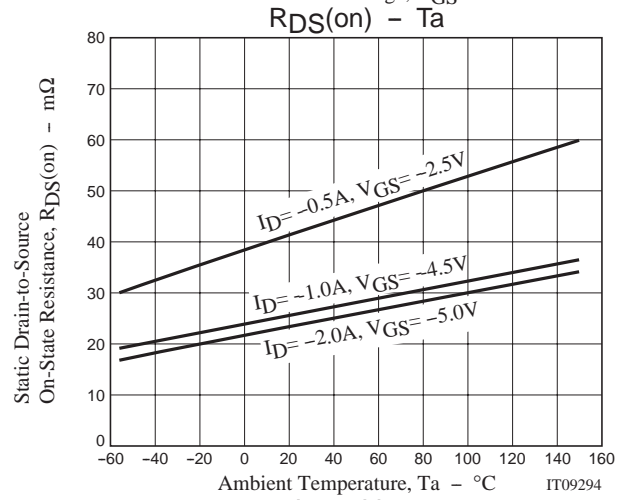
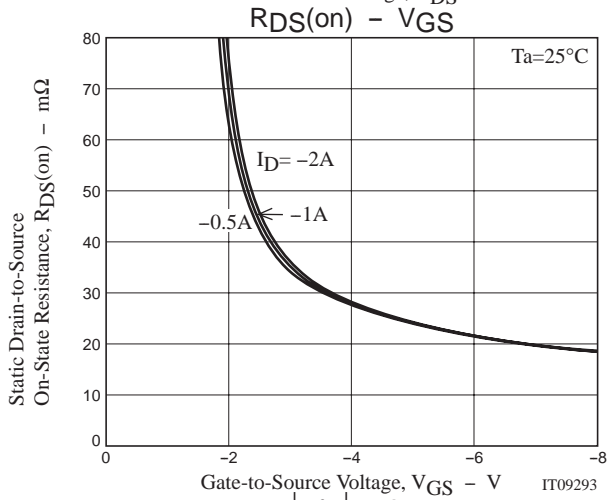
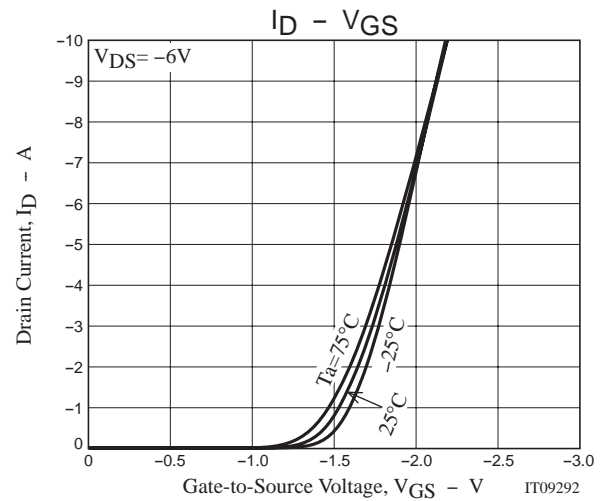
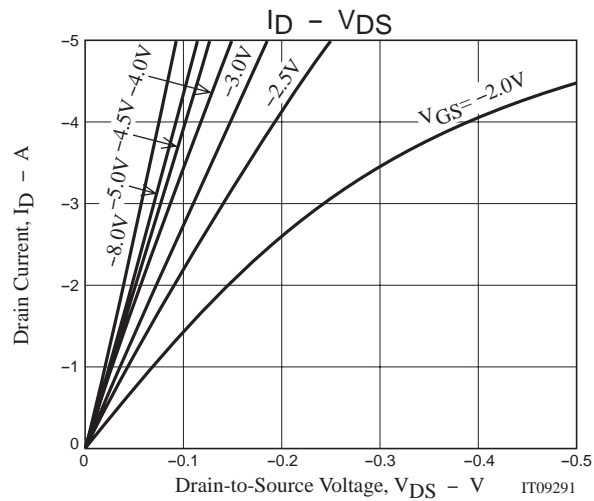


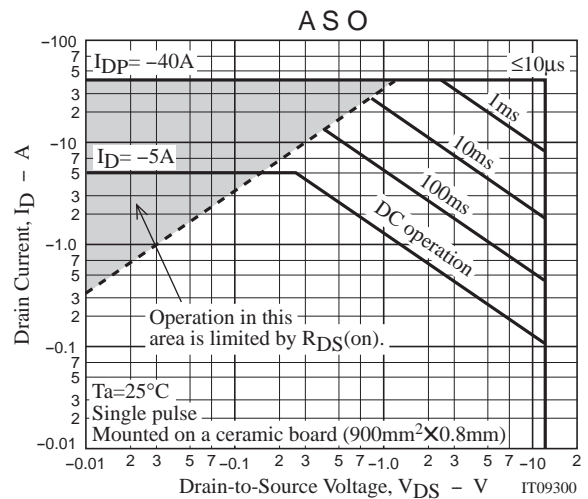
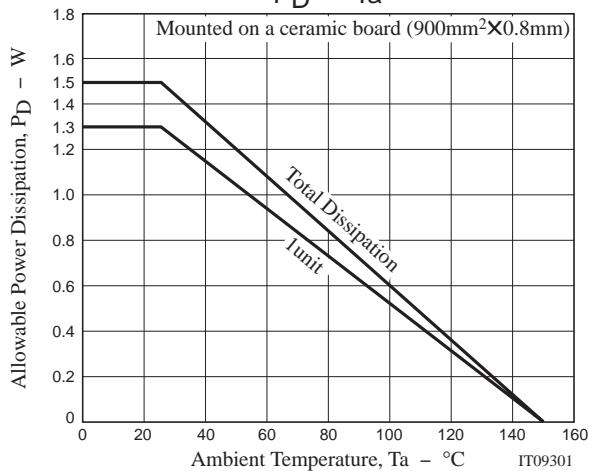
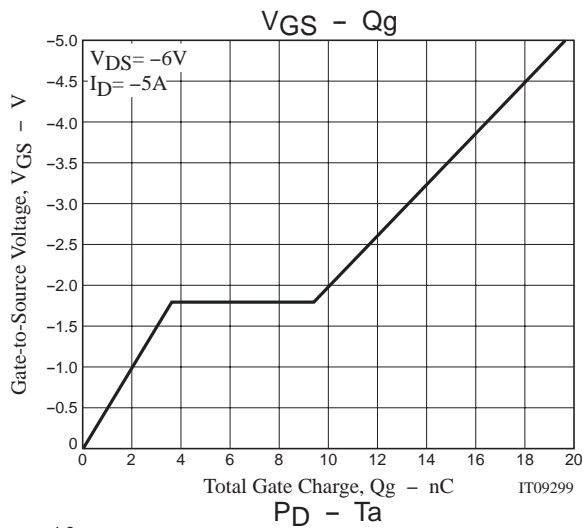
Electrical Connection



Switching Time Test Circuit







Note on usage : Since the ECH8631 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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